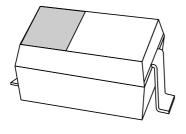
DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG2005AEA; PMEG3005AEA; PMEG4005AEA

Very low V_F MEGA Schottky barrier rectifiers

Product data sheet 2003 Aug 20



Very low V_F MEGA Schottky barrier rectifiers

PMEG2005AEA; PMEG3005AEA; PMEG4005AEA

FEATURES

- · Very low forward voltage
- · High surge current
- Very small plastic SMD package.

APPLICATIONS

- · Low voltage rectification
- High efficiency DC/DC conversion
- Voltage clamping
- · Inverse polarity protection
- Low power consumption applications.

DESCRIPTION

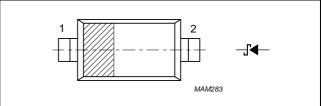
Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD323 (SC-76) very small SMD plastic package.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
I _F	forward current	0.5	Α
V_R	reverse voltage		
	PMEG2005AEA	20	٧
	PMEG3005AEA	30	V
	PMEG4005AEA	40	V

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



The marking bar indicates the cathode.

Fig.1 Simplified outline (SOD323; SC-76) and symbol.

MARKING

TYPE NUMBER	MARKING CODE
PMEG2005AEA	E5
PMEG3005AEA	E4
PMEG4005AEA	E3

RELATED PRODUCTS

TYPE NUMBER	DESCRIPTION	FEATURE
PMEGxx05AEV	0.5 A; 20/30/40 V very low V _F MEGA Schottky rectifier	SOT666 package
PMEG2005EB	0.5 A; 20 V very low V _F MEGA Schottky rectifier	smaller SOD523 (SC-79) package
PMEG2010EA	1 A; 20 V very low V _F MEGA Schottky rectifier	higher forward current

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Very low V_F MEGA Schottky barrier rectifiers

PMEG2005AEA; PMEG3005AEA; PMEG4005AEA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage				
	PMEG2005AEA		_	20	V
	PMEG3005AEA		_	30	V
	PMEG4005AEA		_	40	V
I _F	continuous forward current	note 1	_	0.5	Α
I _{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.5$	_	3.5	Α
I _{FSM}	non-repetitive peak forward current	t _p = 8 ms; square wave	_	10	Α
Tj	junction temperature	note 2	_	150	°C
T _{amb}	operating ambient temperature	note 2	-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

Notes

- 1. Refer to SOD323 (SC-76) standard mounting conditions.
- For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses
 P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and
 I_{F(AV)} rating will be available on request.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air; notes 1 and 2	450	K/W
	ambient	in free air; notes 2 and 3	210	K/W
R _{th j-s}	thermal resistance from junction to soldering point	note 4	90	K/W

Notes

- 1. Refer to SOD323 (SC-76) standard mounting conditions.
- 2. For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.
- 3. Device mounted on an FR4 printed-circuit board with copper clad 10×10 mm.
- 4. Solder point of cathode tab.

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Very low V_F MEGA Schottky barrier rectifiers

PMEG2005AEA; PMEG3005AEA; PMEG4005AEA

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

CVMDOL	DADAMETED	CONDITIONS	PMEG2	005AEA	PMEG3	005AEA	PMEG4	PMEG4005AEA	
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	TYP.	MAX.	TYP.	MAX.	UNIT
V _F	forward voltage	I _F = 0.1 mA	90	130	90	130	95	130	mV
		I _F = 1 mA	150	190	150	200	155	210	mV
		I _F = 10 mA	210	240	215	250	220	270	mV
		I _F = 100 mA	280	330	285	340	295	350	mV
		I _F = 500 mA	355	390	380	430	420	470	mV
I _R	continuous reverse	V _R = 10 V; note 1	15	40	12	30	7	20	μΑ
	current	V _R = 20 V; note 1	40	200	_	_	_	_	μΑ
		V _R = 30 V; note 1	_	_	40	150	_	_	μΑ
		V _R = 40 V; note 1	_	_	_	_	30	100	μΑ
C _d	diode capacitance	V _R = 1 V; f = 1 MHz	66	80	55	70	43	50	pF

Note

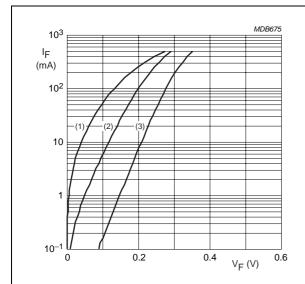
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^{1.} Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

Very low V_F MEGA Schottky barrier rectifiers

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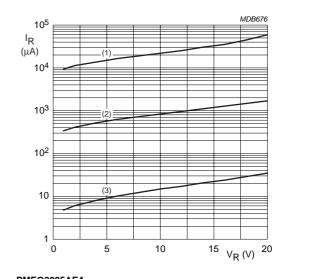
GRAPHICAL DATA



PMEG2005AEA

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

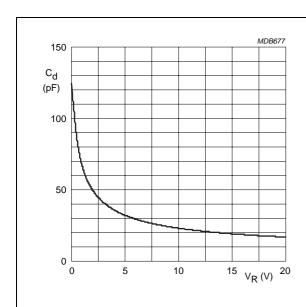
Fig.2 Forward current as a function of forward voltage; typical values.



PMEG2005AEA

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



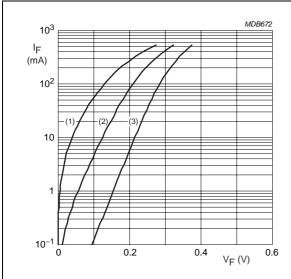
PMEG2005AEA

 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}.$

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

Very low V_F MEGA Schottky barrier rectifiers

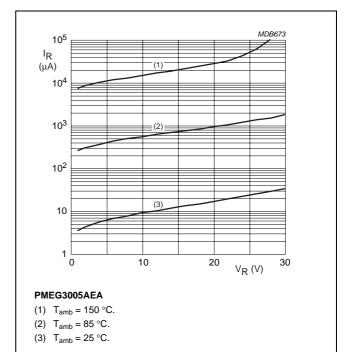
PMEG2005AEA; PMEG3005AEA; PMEG4005AEA



PMEG3005AEA

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.5 Forward current as a function of forward voltage; typical values.



Reverse current as a function of reverse

voltage; typical values.

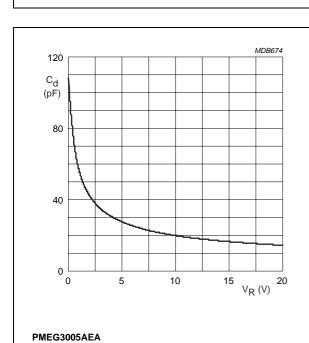
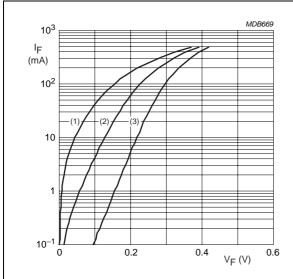


Fig.7 Diode capacitance as a function of reverse voltage; typical values.

f = 1 MHz; T_{amb} = 25 °C.

Very low V_F MEGA Schottky barrier rectifiers

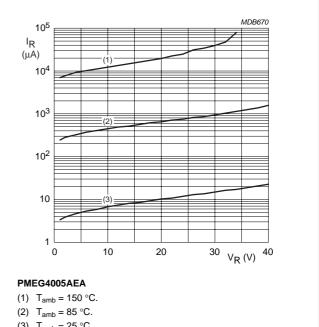
PMEG2005AEA; PMEG3005AEA; PMEG4005AEA



PMEG4005AEA

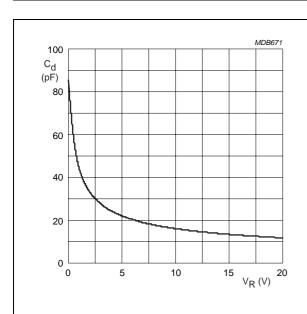
- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.8 Forward current as a function of forward voltage; typical values.



(3) $T_{amb} = 25 \, ^{\circ}C$.

Reverse current as a function of reverse voltage; typical values.



PMEG4005AEA

f = 1 MHz; T_{amb} = 25 °C.

Fig.10 Diode capacitance as a function of reverse voltage; typical values.

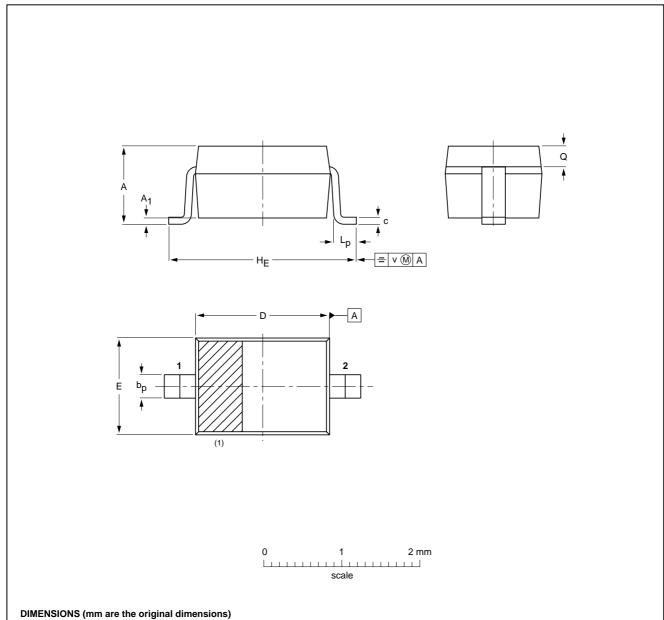
Very low V_F MEGA Schottky barrier rectifiers

PMEG2005AEA; PMEG3005AEA; PMEG4005AEA

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD323



UNIT	Α	A ₁ max.	bp	С	D	E	HE	Lp	Q	٧
mm	1.1 0.8	+ 0.05 - 0.05	0.40 0.25	0.25 0.10	1.8 1.6	1.35 1.15	2.7 2.3	0.45 0.15	0.25 0.15	0.2

Note

1. The marking bar indicates the cathode.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOD323			SC-76			98-09-14 99-09-13

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Very low V_F MEGA Schottky barrier rectifiers

PMEG2005AEA; PMEG3005AEA; PMEG4005AEA

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
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Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
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